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SANYO Semiconductors DATA SHEET

4MN10CH — High-Frequency General-Purpose Amplifier Applications

Features

- High fT: fT=400MHz (typ).
- · High breakdown voltage: VCEO≥200V.
- Small reverse transfer capacitance and excellent high-frequnecy characteristic : Cre=1.4pF.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		200	V
Collector-to-Emitter Voltage	VCEO		200	V
Emitter-to-Base Voltage	VEBO		4	V
Collector Current	IC		100	mA
Collector Current (Pulse)	ICP		200	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm ² X0.8mm)	600	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

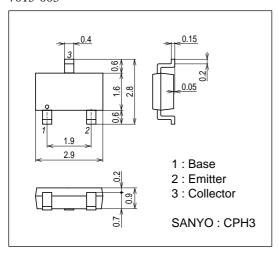
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =150V, I _E =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=2V, IC=0A			1.0	μΑ
DC Current Gain	hFE1	V _{CE} =10V, I _C =10mA	60		200	
	hFE2	V _{CE} =10V, I _C =60mA	20			
Gain-Bandwideth Product	fT	VCE=30V, IC=30mA		400		MHz
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =30mA, I _B =3mA			0.6	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0A	200			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	200			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =100μA, I _C =0A	4			V
Output Capacitance	Cob	V _{CB} =30V, f=1MHz		1.8		pF
Reverse Transfer Capacitance	Cre	VCB=30V, f=1MHz		1.4		pF

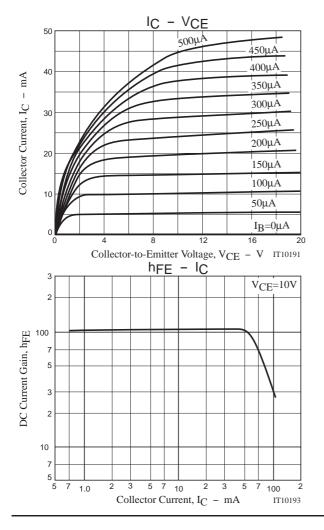
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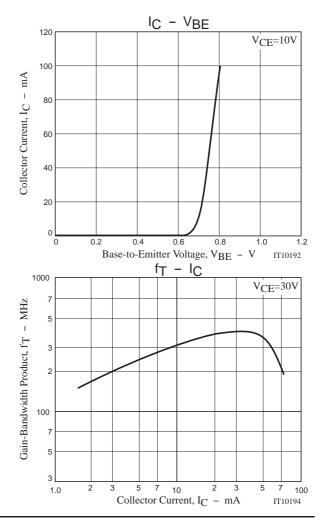
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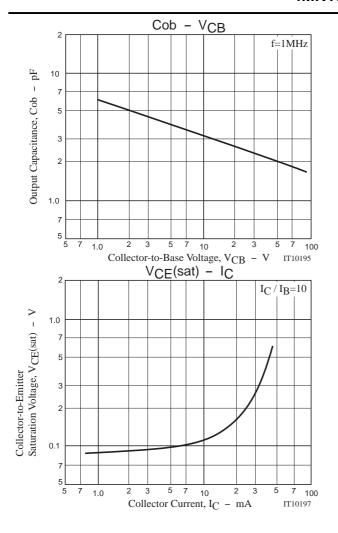
Package Dimensions

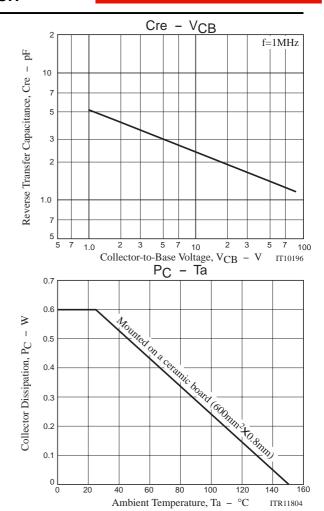
unit : mm 7015-003











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